SHANGHAI SUNRISE ELECTRONICS CO., LTD.

SB85

SILICON SCHOTTKY
DETECTING DIODE

REVERSE VOLTAGE: 50V
FORWARD CURRENT: 150mA

TECHNICAL SPECIFICATION

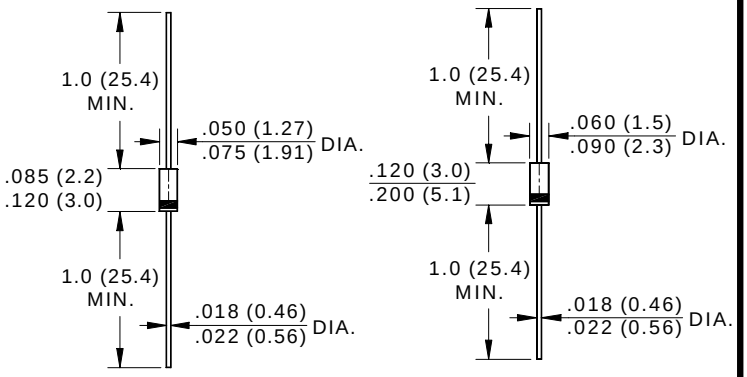
FEATURES

- Small glass structure ensures high reliability
- Fast switching
- Low leakage
- High temperature soldering guaranteed: 250°C/10S/9.5mm lead length at 5 lbs tension

MECHANICAL DATA

- Terminal: Plated axial leads solderable per MIL-STD 202E, method 208C
- Case: Glass,hermetically sealed
- Polarity: Color band denotes cathode
- Mounting position: Any

DO - 34 **DO - 35**



Dimensions in inches and (millimeters)

MAXIMUM RATINGS AND CHARACTERISTICS

(Ratings at 25°C ambient temperature unless otherwise specified)

RATINGS		SYMBOL	VALUE		UNITS
			Typ.	Max.	
Reverse Voltage		V_R		50	V
Forward Current (peak)		I_{FM}		150	mA
Forward Current (D.C.)		I_F		30	mA
Forward Voltage (D.C.)	I_F=10mA	V_{F1}		0.4	V
	I_F=100mA	V_{F2}		0.8	V
Reverse Current (V_R=30V)		I_R		3	μA
Capacitance (Note 1)		Ct	6		pF
Detection Effectiveness (Note 2)		η	60%		
Operating Junction and Storage Temperature Range		T_J,T_{STG}	-55～+125		°C

Notes:

1. VR=10V, f=1MHz
2. Vm=3V(peak), f=30MHz, RL=3.9KΩ, Ct=10pF.